

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L7	1879	(438/270).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/19 16:58
L8	546	7 and ((first and second) near4 (conducti\$4 type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/19 16:59
L9	241	8 and ((ion impurit\$4 atom) near3 implant\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/19 17:39
L10	134	(438/273).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/19 17:34
L11	380	(438/546).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/19 17:37
L13	2370	((438/270) or (438/273) or (438/546)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/19 17:38
L14	616	13 and (mosfet (metal adj oxide adj semiconductor adj field adj effect adj transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/19 17:38
L15	583	14 and @ad<"20040318"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/19 17:39

L16	296	15 and ((ion impurit\$4 atom) near3 implant\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/19 17:44
L17	140	13 and (ar argon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/19 17:45
S1	2	("2004304155").PN.	JPO; DERWENT	OR	OFF	2005/10/17 13:21
S2	5	("3238870").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 13:22
S3	3181	vertical near3 (mosfet (metal adj oxide adj semiconductor adj field adj effect adj transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/19 17:38
S4	1281	S3 and ((first and second) near2 (conducti\$4 type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/19 16:59
S5	985	S4 and (gate near2 electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 15:12
S6	925	S5 and @ad<"20040318"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/19 17:39
S7	748	S6 and (insulat\$4 near3 (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/17 15:15

S8	366	S7 and ((ion impurit\$4 atom) near3 implant\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/19 17:00
S9	0	("2004/0016963").URPN.	USPAT	OR	ON	2005/10/17 15:32
S10	3184	vertical near3 (mosfet (metal adj oxide adj semiconductor adj field adj effect adj transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/18 12:35
S11	1283	S10 and ((first and second) near2 (conducti\$4 type))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/18 12:36
S12	1211	S11 and @ad<"20040318"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/18 12:36
S13	477	S12 and ((ion impurit\$4 atom) near3 implant\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/18 16:08
S14	31	S13 and (trench near6 (pierc\$3 reach\$3 open\$3) near5 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/18 14:31
S15	1	S14 and ((Ar argon) and (phospho\$4 arsen\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/18 14:32
S16	29	S13 and ((Ar argon) and (phospho\$4 arsen\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/18 14:55
S17	2	("5045900" "5282018").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/18 14:37

S18	26	("5814858").URPN.	USPAT	OR	ON	2005/10/18 14:38
S19	42	S13 and (Ar argon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/18 16:08
S20	1	S12 and ((Ar argon) near3 (ion impurit\$4 atom) near3 implant\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/18 15:15
S21	3	S12 and ((Ar argon) near3 implant\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/18 15:15
S22	961	S12 and (ion impurit\$4 atom)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/18 16:08
S23	51	S22 and (Ar argon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/18 16:08